AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A method of forming a gate electrode in a semiconductor, comprising:

forming a polysilicon film and a ~~metal~~ tungsten silicide film sequentially on a semiconductor substrate;

performing an annealing process to crystallize the ~~metal~~ tungsten silicide film; and

~~forming a gate electrode by performing a single etching process on the metal tungsten silicide film and the polysilicon film~~ performing an etching process to etch the tungsten silicide film and the polysilicon film under the tungsten silicide film using the same etching gas, thereby forming a gate electrode comprising the tungsten silicide film and the polysilicon film.

2. (Currently Amended) The method of forming a gate electrode in a semiconductor according to claim 1, wherein the annealing process is one of ~~an~~ a rapid thermal process (RTP) annealing process and a furnace annealing process for crystallizing an amorphous ~~metal~~ tungsten silicide film to form a crystalline ~~metal~~ tungsten silicide film.

3. (Currently Amended) The method of forming a gate electrode in a semiconductor according to claim 2, ~~wherein~~ comprising performing the RTP annealing process ~~is performed~~ at a temperature ranging from about 900°C to about 1000°C for a time period ranging from about 10 seconds to about 30 seconds in an ambient atmosphere of N_2 or NH_3 gas, and ~~wherein~~ performing the furnace annealing process ~~is performed~~ at a temperature ranging from about 850°C to about 1000°C for a time period ranging from about 5 minutes to about 30 minutes in an ambient of N_2 or NH_3 gas.

4. (Canceled)

5. (Currently Amended) The method of forming a gate electrode in a semiconductor according to claim 1, ~~wherein~~ comprising performing the etching process ~~is performed~~ under a process condition for etching the polysilicon film.

6. (Currently Amended) The method of forming a gate electrode in a semiconductor according to claim 5, wherein the etching process is a dry etching process ~~which is performed~~, and comprising performing the etching process in an inductively coupled plasma chamber into which a mixture gas of Cl_2 gas and O_2 gas is introduced.

7. (Currently Amended) The method of forming a gate electrode in a semiconductor according to claim 1, wherein the etching process is a dry etching process ~~which is performed~~, and comprising performing the etching process in an inductively coupled plasma chamber into which a mixture gas of Cl_2 gas and O_2 gas is introduced.

8. (Original) The method of forming a gate electrode in a semiconductor according to claim 1, where in the annealing process results in the etch rate of the crystallized metal silicide film being similar to that of the polysilicon film

9. (New) The method of forming a gate electrode in a semiconductor according to claim 1, comprising forming the tungsten silicide film by reacting SiH_4 or SiH_2Cl_2 with WF_6 at a stochiometric ratio of (SiH_4 or SiH_2Cl_2): WF_6 of 2.0 - 2.8.